



GP
ELECTRONICS

DTC114EE

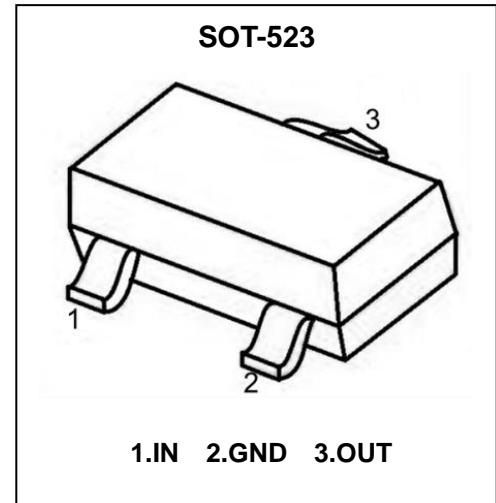
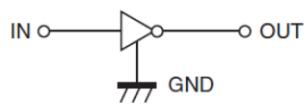
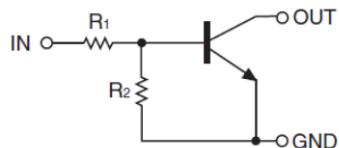
Digital Transistor

DTC114EE Digital Transistor(NPN)

Feature

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors
- The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input .They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy

Schematic diagram



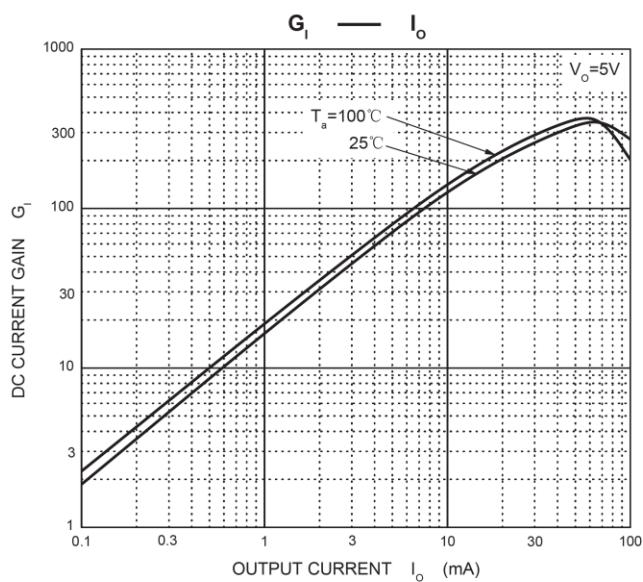
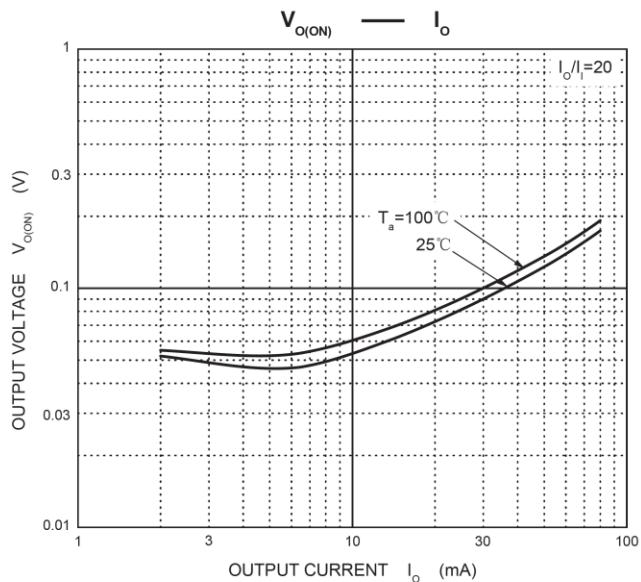
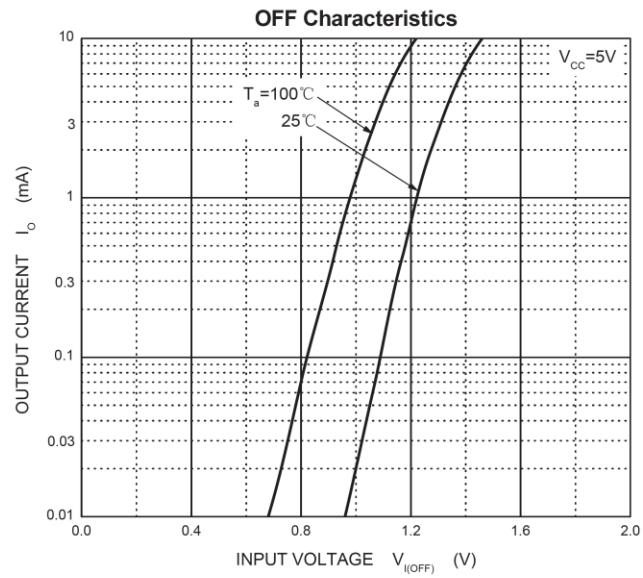
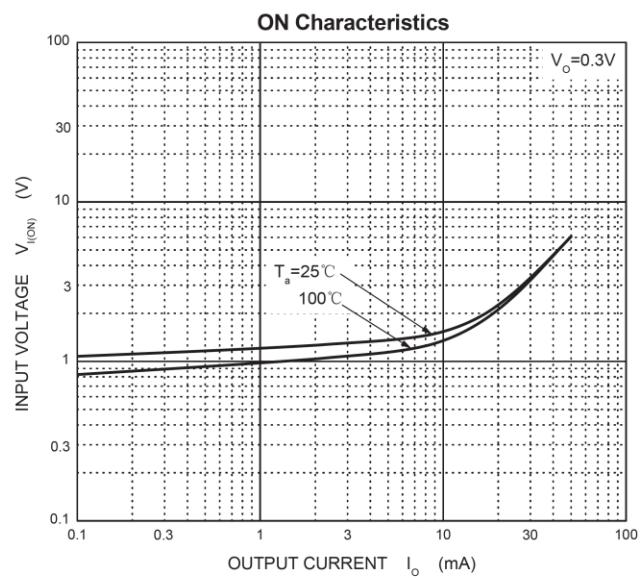
ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

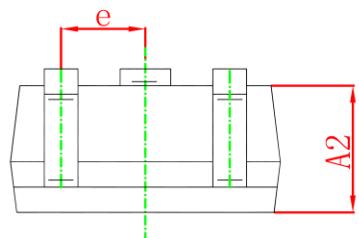
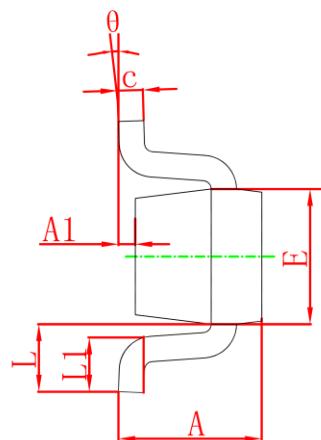
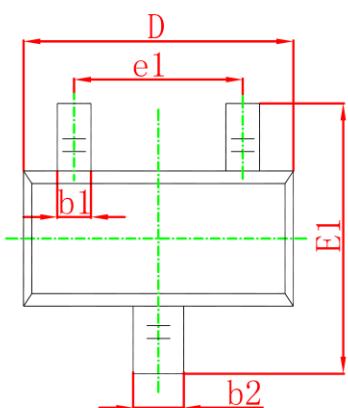
Parameter	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-10~+40	V
Output Current	I _O	100	mA
Power Dissipation	P _D	150	mW
Junction Temperature	T _J	125	°C
Storage Temperature Range	T _{STG}	-45 ~ +125	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Input voltage	V _{I(off)}	V _{CC} =5V , I _O =100μA	0.5			V
	V _{I(on)}	V _O =0.3V , I _O =10mA			3	V
Output voltage	V _{O(on)}	I _O =10mA , I _I =0.5mA			0.3	V
Input current	I _I	V _I =5V			0.88	mA
Output current	I _{O(off)}	V _{CC} =50V , V _I =0V			0.5	μA
DC current gain	G _I	V _O =5V , I _O =5mA	30			
Input resistance	R _I		7	10	13	kΩ
Resistance ratio	R ₂ / R ₁		0.8	1	1.2	
Transition frequency	f _T	V _O =10V,I _O =5mA,f=1MHz		250		MHz

Typical Characteristics



SOT-523 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°